800V Single-Pole, Normally Open Power Relay

Characteristics

Parameter	Rating	Units
Blocking Voltage	800	V _P
Load Current, T _A =25°C:		
With 5°C/W Heat Sink	1.85	A _{rms} / A _{DC}
No Heat Sink	0.75	7rms / 7DC
On-Resistance (max)	2.3	Ω
Thermal Impedance, Junction-to-Case, θ_{JC}	0.35	°C/W

Features

- 1.85A_{rms} Load Current with 5°C/W Heat Sink
- Low 2.3Ω On-Resistance
- 800V_P Blocking Voltage
- 2500V_{rms} Input/Output Isolation
- Low Thermal Impedance: θ_{JC} = 0.35 °C/W
- Isolated, Low Thermal Impedance Ceramic Pad for Heat Sink Applications
- Low Drive Power Requirements
- Arc-Free With No Snubbing Circuits
- No EMI/RFI Generation
- Flammability Rating UL 94 V-0

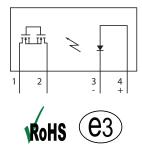
Applications

- Industrial Controls / Motor Control
- Robotics
- Medical Equipment—Patient/Equipment Isolation
- Instrumentation
- Multiplexers
- Data Acquisition
- Electronic Switching
- I/O Subsystems
- Meters (Watt-Hour, Water, Gas)
- Transportation Equipment
- Aerospace/Defense

Approvals

UL 508 Recognized Component: File E69938

Pin Configuration



Description

IXYS Integrated Circuits brings OptoMOS® technology, reliability and compact size to a new family of high-power Solid State Relays.

As part of this family, the CPC1978 single-pole normally open (1-Form-A) Solid State Power Relay is rated for up to $1.85A_{rms}$ continuous load current with a 5°C/W heat sink.

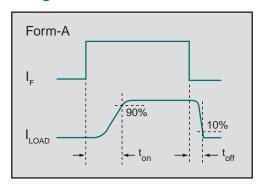
The CPC1978 employs optically coupled MOSFET technology to provide 2500V_{rms} of input to output isolation. The optically coupled outputs, that use patented OptoMOS architecture, are controlled by a highly efficient infrared LED. The combination of low on-resistance and high load current handling capability makes this relay suitable for a variety of high performance switching applications.

The unique i4-PAC package pioneered by IXYS enables Solid State Relays to achieve the highest load current and power ratings. This package features a unique IXYS process where the silicon chips are soft soldered onto the Direct Copper Bond (DCB) substrate instead of the traditional copper leadframe. The DCB ceramic, the same substrate used in high power modules, not only provides 2500V_{rms} isolation but also very low junction-to-case thermal impedance (0.35 °C/W).

Ordering Information

Part	Description
CPC1978J	i4-PAC Package (25 per tube)

Switching Characteristics





1 Specifications

1.1 Absolute Maximum Ratings @ 25°C

Symbol	Ratings	Units
Blocking Voltage	800	V_{P}
Reverse Input Voltage	5	V
Input Control Current	100	mA
Peak (10ms)	1	Α
Input Power Dissipation	150	mW
Isolation Voltage, Input to Output	2500	V_{rms}
Operational Temperature	-40 to +85	°C
Storage Temperature	-40 to +125	°C

Absolute maximum ratings are stress ratings. Stresses in excess of these ratings can cause permanent damage to the device. Functional operation of the device at conditions beyond those indicated in the operational sections of this data sheet is not implied.

Typical values are characteristic of the device at +25°C, and are the result of engineering evaluations. They are provided for information purposes only, and are not part of the manufacturing testing requirements.

1.2 Electrical Characteristics @ 25°C

Parameter	Conditions	Symbol	Minimum	Typical	Maximum	Units
Output Characteristics						
Load Current ¹						
Peak	t≤10ms				10	A_P
Continuous	No Heat Sink	ΙL			0.75	A _{rms} / A _{DC}
Continuous	T _C =25°C		-	-	7.25	
Continuous	T _C =99°C	I _{L(99)}			0.825	
On-Resistance ²	I _F =10mA, I _L =1A	R _{ON}	-	1.7	2.3	Ω
Off-State Leakage Current	V _L =800V _P	I _{LEAK}	-	-	1	μА
Switching Speeds						
Turn-On	I _F =20mA, V _I =10V	t _{on}	-	8	20	
Turn-Off	1F-20111A, V[-10V	t _{off}	-	0.15	5	ms
Output Capacitance	I _F =0mA, V _L =25V, f=1MHz	C _{out}	-	390	-	pF
Input Characteristics					+	
Input Control Current to Activate ³	I _L =1A	I _F	-	-	10	mA
Input Control Current to Deactivate	-	I _F	0.6	-	-	mA
Input Voltage Drop	I _F =10mA	V _F	0.9	1.35	1.56	V
Reverse Input Current	V _R =5V	I _R	-	-	10	μΑ
Input/Output Characteristics					1	
Capacitance, Input-to-Output	V _{IO} =0V, f=1MHz	C _{IO}	-	1	-	pF

¹ Higher load currents possible with proper heat sinking.

² Measurement taken within 1 second of on-time.

 $^{^3}$ For applications requiring high temperature operation (T_C > 60°C) a minimum LED drive current of 20mA is recommended.



Thermal Characteristics

Parameter	Conditions	Symbol	Rating	Units
Thermal Impedance (Junction to Case)	-	θЈС	0.35	°C/W
Thermal Impedance (Junction to Ambient)	Free Air	$\theta_{\sf JA}$	33	°C/W
Junction Temperature (Operating)	-	TJ	-40 to +100	°C

2.1 Thermal Management

Device high current characterization was performed using Kunze heat sink KU 1-159, phase change thermal interface material KU-ALC 5, and transistor clip KU 4-499/1. This combination provided an approximate junction-to-ambient thermal impedance of 12.5°C/W.

2.2 Heat Sink Calculation

Higher load currents are possible by using lower thermal impedance heat sink combinations.

Heat Sink Rating

$$\theta_{CA} = \frac{(T_J - T_A) I_{L(99)}^2}{I_L^2 - P_{D(99)}} - \theta_{JC}$$

 $T_J = Junction Temperature (°C), T_J \le 100°C$ *

 T_{Δ} = Ambient Temperature (°C)

 $I_{L(99)}$ = Load Current with Case Temperature @ 99°C (A_{DC})

 $I_L^{(99)}$ = Desired Operating Load Current (A_{DC}), $I_L \le I_{L(MAX)}$ θ_{JC} = Thermal Impedance, Junction to Case (°C/W) = 0.35°C/W

 $\theta_{CA}^{\circ\circ}$ = Thermal Impedance of Heat Sink & Thermal Interface Material , Case to Ambient (°C/W)

 $P_{D(99)}^{CA}$ = Maximum power dissipation with case temperature held at 99°C = 2.86W

NOTE: The exposed surface of the DCB substrate is not to be soldered.

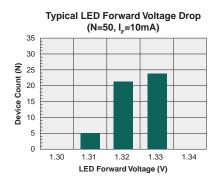
3 R10 www.ixysic.com

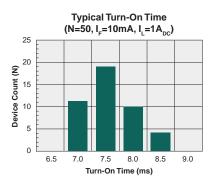
^{*} Elevated junction temperature reduces semiconductor lifetime.

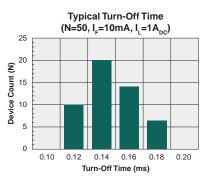


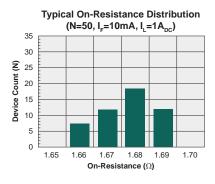
3 Performance Data*

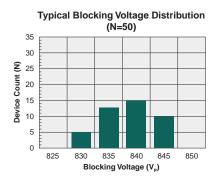
Unless otherwise specified, all performance data was acquired without the use of a heat sink.

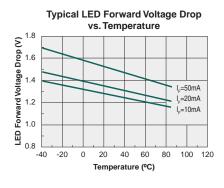


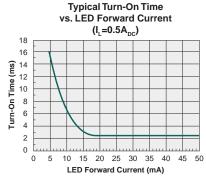


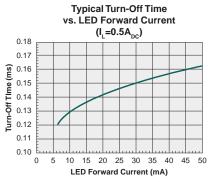


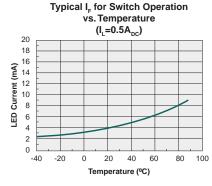


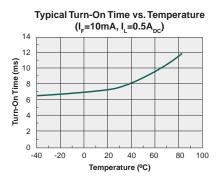


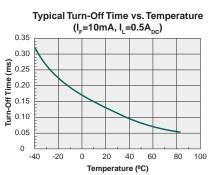






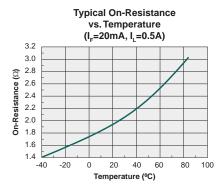


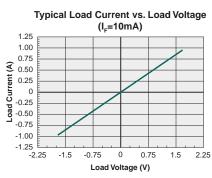


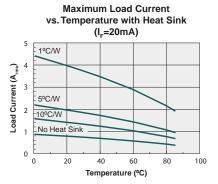


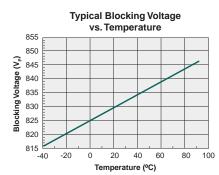
*Unless otherwise noted, data presented in these graphs is typical of device operation at 25°C. For guaranteed parameters not indicated in the written specifications, please contact our application department.

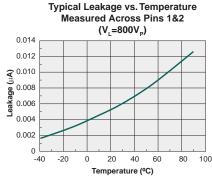


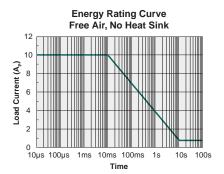












*Unless otherwise noted, data presented in these graphs is typical of device operation at 25°C. For guaranteed parameters not indicated in the written specifications, please contact our application department.



4 Manufacturing Information

4.1 Moisture Sensitivity



All plastic encapsulated semiconductor packages are susceptible to moisture ingression. IXYS Integrated Circuits classifies its plastic encapsulated devices for moisture sensitivity according to the latest version of the joint industry standard, **IPC/JEDEC J-STD-020**, in force at the time of product evaluation. We test all of our products to the maximum conditions set forth in the standard, and guarantee proper operation of our

devices when handled according to the limitations and information in that standard as well as to any limitations set forth in the information or standards referenced below.

Failure to adhere to the warnings or limitations as established by the listed specifications could result in reduced product performance, reduction of operable life, and/or reduction of overall reliability.

This product carries a **Moisture Sensitivity Level (MSL)** classification as shown below, and should be handled according to the requirements of the latest version of the joint industry standard **IPC/JEDEC J-STD-033**.

Device	Moisture Sensitivity Level (MSL) Classification
CPC1978J	MSL 1

4.2 ESD Sensitivity



This product is ESD Sensitive, and should be handled according to the industry standard JESD-625.

4.3 Soldering Profile

Provided in the table below is the Classification Temperature (T_C) of this product and the maximum dwell time the body temperature of this device may be $(T_C - 5)^{\circ}C$ or greater. The classification temperature sets the Maximum Body Temperature allowed for this device during lead-free reflow processes. For through-hole devices, and any other processes, the guidelines of **J-STD-020** must be observed.

Device	Classification Temperature (T _C)	Dwell Time (t _p)	Max Reflow Cycles
CPC1978J	245°C	30 seconds	1

NOTE: The exposed surface of the DCB substrate is not to be soldered.

4.4 Board Wash

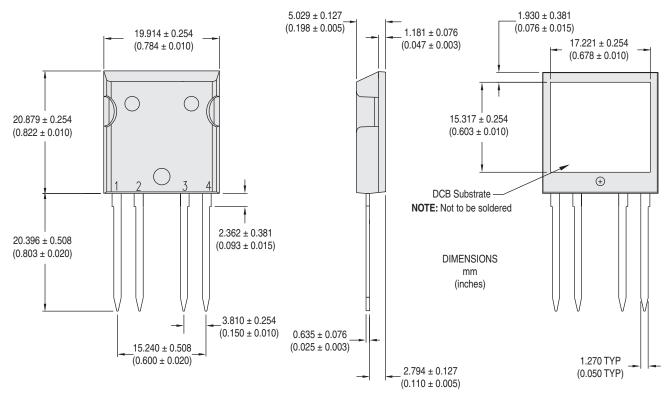
IXYS Integrated Circuits recommends the use of no-clean flux formulations. Board washing to reduce or remove flux residue following the solder reflow process is acceptable provided proper precautions are taken to prevent damage to the device. These precautions include but are not limited to: using a low pressure wash and providing a follow up bake cycle sufficient to remove any moisture trapped within the device due to the washing process. Due to the variability of the wash parameters used to clean the board, determination of the bake temperature and duration necessary to remove the moisture trapped within the package is the responsibility of the user (assembler). Cleaning or drying methods that employ ultrasonic energy may damage the device and should not be used. Additionally, the device must not be exposed to flux or solvents that are Chlorine- or Fluorine-based.







4.5 Mechanical Dimensions



NOTE: Metallized external surface of DCB substrate maintains 2500V_{rms} isolation to device internal structure and all external pins.

For additional information please visit our website at: www.ixysic.com

IXYS Integrated Circuits makes no representations or warranties with respect to the accuracy or completeness of the contents of this publication and reserves the right to make changes to specifications and product descriptions at any time without notice. Neither circuit patent licenses nor indemnity are expressed or implied. Except as set forth in IXYS Integrated Circuits' Standard Terms and Conditions of Sale, IXYS Integrated Circuits assumes no liability whatsoever, and disclaims any express or implied warranty, relating to its products including, but not limited to, the implied warranty of merchantability, fitness for a particular purpose, or infringement of any intellectual property right.

The products described in this document are not designed, intended, authorized or warranted for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or where malfunction of IXYS Integrated Circuits' product may result in direct physical harm, injury, or death to a person or severe property or environmental damage. IXYS Integrated Circuits reserves the right to discontinue or make changes to its products at any time without notice.

Specification: DS-CPC1978-R10 ©Copyright 2018, IXYS Integrated Circuits All rights reserved. Printed in USA. 6/21/2018